

## **KSC815**

# Low Frequency Amplifier & High Frequency Oscillator

- Collector-Base Voltage : V<sub>CBO</sub>=60V
- Complement to KSA539
- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)



## **NPN Epitaxial Silicon Transistor**

## **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V <sub>CBO</sub>	Collector-Base Voltage	60	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	45	V	
V <sub>EBO</sub>	Emitter-Base Voltage	5	V	
I <sub>C</sub>	Collector Current	200	mA	
P <sub>C</sub>	Collector Power Dissipation	400	mW	
T <sub>J</sub>	Junction Temperature	150	°C	
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C	

### Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C=100\mu A, I_E=0$	60			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =0	45			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E=10\mu A, I_C=0$	5			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB}$ =45V, $I_{E}$ =0			0.1	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB}$ =3V, $I_{C}$ =0			0.1	μΑ
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> =1V, I <sub>C</sub> =50mA	40		400	
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA	0.6	0.65	0.9	V
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =150mA, I <sub>B</sub> =15mA		0.15	0.4	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> =150mA, I <sub>B</sub> =15mA		0.83	1.1	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA	100	200		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		4		pF

## **h**<sub>FE</sub> Classification

Classification	R	0	Y	G	
h <sub>FE</sub>	40 ~ 80	70 ~ 140	120 ~ 240	200 ~ 400	

## **Typical Characteristics**

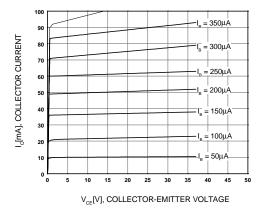


Figure 1. Static Characteristic

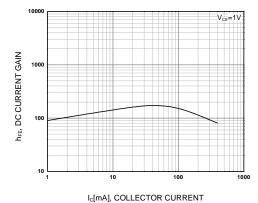


Figure 2. DC current Gain

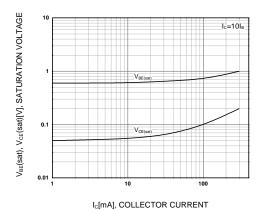


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

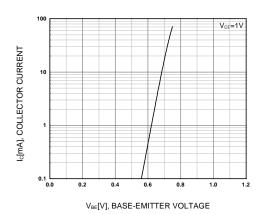


Figure 4. Base-Emitter On Voltage

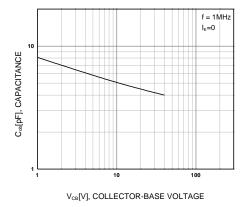


Figure 5. Collector Output Capacitance

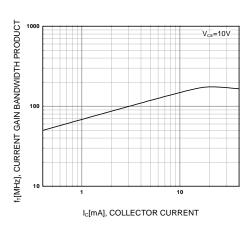
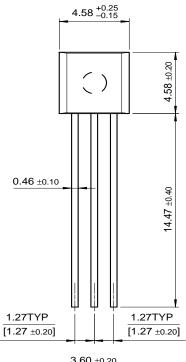


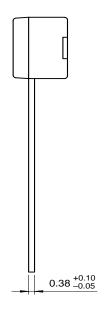
Figure 6. Current Gain Bandwidth Product

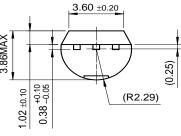
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## **Package Dimensions**

TO-92







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CoolFET™	FASTr™	MicroFET™	PowerTrench <sup>®</sup>	SuperSOT™-6
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DOME™	GlobalOptoisolator™	MICROWIRE™	$QS^{TM}$	SyncFET™
EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic™
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EnSigna™	$I^2C^{TM}$	$OCX^{TM}$	RapidConfigure™	UHC™
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